

**PROCESS FOR MONITORING THE GASEOUS
ENVIRONMENT OF A CRYSTAL PULLER
FOR SEMICONDUCTOR GROWTH**

ABSTRACT OF THE INVENTION

5 This invention relates to a process for monitoring the gaseous environment within a sealed crystal pulling furnace, used for the growth of an ingot of a semiconductor material in a growth chamber maintained at a sub-atmospheric pressure. The process comprises sealing the chamber, 10 reducing the pressure within the sealed chamber to a sub-atmospheric level, introducing a process gas into the chamber to purge the chamber and form a gaseous environment therein, and analyzing the gaseous environment within the chamber for the presence of a contaminant gas in a concentration which is greater than the concentration of the 15 contaminant gas in the process gas.